

Matthias Wieneke

List of Publications by Year in descending order

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26
papers

300
citations

840776

11
h-index

839539

18
g-index

26
all docs

26
docs citations

26
times ranked

450
citing authors

#	ARTICLE	IF	CITATIONS
1	InGaN/GaN light-emitting diodes on Si(110) substrates grown by metal-organic vapour phase epitaxy. Journal Physics D: Applied Physics, 2009, 42, 055107.	2.8	35
2	Growth and coalescence behavior of semipolar $(11\bar{2}2)$ GaN on pre-structured a -plane sapphire substrates. Physica Status Solidi (B): Basic Research, 2011, 248, 588-593.	1.5	34
3	Anisotropy of effective electron masses in highly doped nonpolar GaN. Applied Physics Letters, 2013, 103, .	3.3	33
4	Valence-band splitting and optical anisotropy of AlN. Physica Status Solidi (B): Basic Research, 2010, 247, 1679-1682.	1.5	26
5	Leakage currents and Fermi-level shifts in GaN layers upon iron and carbon-doping. Journal of Applied Physics, 2017, 122, .	2.5	23
6	Eliminating stacking faults in semi-polar GaN by AlN interlayers. Applied Physics Letters, 2011, 99, 021905.	3.3	22
7	Ge as a surfactant in metal-organic vapor phase epitaxy growth of a -plane GaN exceeding carrier concentrations of 10^{20}cm^{-3} . Applied Physics Letters, 2013, 103, .	3.3	18
8	Metalorganic vapor-phase epitaxy of GaN layers on Si substrates with Si(110) and other high-index surfaces. Journal of Crystal Growth, 2010, 312, 180-184.	1.5	17
9	Heavy Si doping: The key in heteroepitaxial growth of a -plane GaN without basal plane stacking faults?. Physica Status Solidi (B): Basic Research, 2011, 248, 578-582.	1.5	17
10	Optical anisotropy of A - and M -plane InN grown on free-standing GaN substrates. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1062-1065.	1.8	15
11	Microstructural anisotropy of a -plane GaN analyzed by high resolution X-ray diffraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S498.	0.8	12
12	Influence of anisotropic strain on excitonic transitions in a -plane GaN films. Microelectronics Journal, 2009, 40, 322-324.	2.0	10
13	Valence band tomography of wurtzite GaN by spectroscopic ellipsometry. Applied Physics Express, 2018, 11, 101001.	2.4	10
14	Characterization of defects in undoped non c -plane and high resistance GaN layers dominated by stacking faults. Physica B: Condensed Matter, 2009, 404, 4922-4924.	2.7	7
15	Direct microscopic correlation of crystal orientation and luminescence in spontaneously formed nonpolar and semipolar GaN growth domains. Applied Physics Letters, 2010, 96, .	3.3	6
16	Observation of individual stacking faults in GaN microcrystals by x-ray nanodiffraction. Applied Physics Letters, 2017, 110, .	3.3	6
17	The impurity size-effect and phonon deformation potentials in wurtzite GaN. Semiconductor Science and Technology, 2020, 35, 095033.	2.0	4
18	a -plane GaN Shear Wave Thin Film Resonator. Frequency Control Symposium and Exhibition, Proceedings of the IEEE International, 2007, , .	0.0	2

#	ARTICLE	IF	CITATIONS
19	Nanoscale cathodoluminescence of stacking faults and partial dislocations in <i>a</i> -plane GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 73-77.	1.5	2
20	Unintentional doping of <i>a</i> -plane GaN by insertion of <i>in situ</i> SiN masks. <i>Journal Physics D: Applied Physics</i> , 2011, 44, 085102.	2.8	1
21	High-overtone bulk acoustic wave resonator on gallium nitride. , 2009, , .		0
22	X-ray Study of Step Induced Lateral Correlation Lengths in Thin AlGa _N Nucleation Layers. <i>Japanese Journal of Applied Physics</i> , 2010, 49, 025503.	1.5	0
23	Optical characterization of a InGa _N /Ga _N microcavity with epitaxial AlInN/Ga _N bottom DBR. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1396, .	0.1	0
24	Optical anisotropy of <i>a</i> -plane Al _{0.8} In _{0.2} N grown on an <i>a</i> -plane Ga _N pseudosubstrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 29-32.	1.8	0
25	Impact of AlN/Si Nucleation Layers Grown Either by NH ₃ -MBE or MOCVD on the Properties of AlGa _N /Ga _N HFETs. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700638.	1.8	0
26	Raman tensor determination of transparent uniaxial crystals and their thin films – <i>a</i> -plane Ga _N as exemplary case. <i>Applied Physics Letters</i> , 2021, 119, 121109.	3.3	0